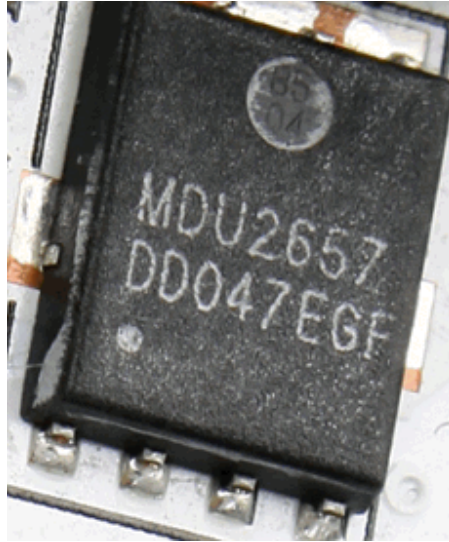


MDU2657



Part Number : MDU2657

Function : Single N-channel Trench MOSFET 30V, 61.7A, 7.5mOhm

Manufacturers : MagnaChip

Description

The device uses advanced Magnachip's MOSFET technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDU2657 is suitable device for DC/DC converter and general purpose application.

Features

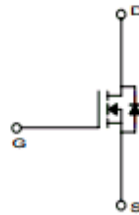
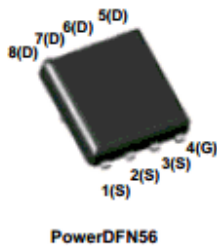
1. $V_{ds} = 30V$
2. $I_d = 61.7A @ V_{gs} = 10V$

General Description

The MDU2657 uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDU2657 is suitable device for DC/DC Converter and general purpose applications.

Features

- $V_{DS} = 30V$
- $I_D = 61.7A$ @ $V_{GS} = 10V$
- $R_{DS(on)} < 7.5m\Omega$ @ $V_{GS} = 10V$
- $R_{DS(on)} < 11.3m\Omega$ @ $V_{GS} = 4.5V$
- 100% U.I.L. Tested
- 100% Rg Tested



Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_c=25^\circ C$	61.7
		$T_c=70^\circ C$	49.3
		$T_A=25^\circ C$	20.4 ^(R)
		$T_A=70^\circ C$	16.3 ^(R)
Pulsed Drain Current	I_{DM}	100	A
Power Dissipation	P_D	$T_c=25^\circ C$	50
		$T_c=70^\circ C$	32
		$T_A=25^\circ C$	5.5 ^(R)
		$T_A=70^\circ C$	3.5 ^(R)
Single Pulse Avalanche Energy ⁽²⁾	E_{AS}	81	mJ
Junction and Storage Temperature Range	T_J, T_{stg}	-55-150	°C

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	22.7	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	